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Feasibility of Superconductivity in Semiconductor Superlattices

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1. D. R. Harshman and A. P. Mills, *Concerning the nature of high-T_c superconductivity*, Phys. Rev. B 45, 707 (1992).
2. G. Snider, *1D Poisson/Schrödinger User's Manual: A Band Diagram Calculator*, (<http://www.nd.edu/~gsnider>, Univ. Notre Dame, Notre Dame, Indiana).

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